

(93) ((channel with ((bl bitline bit adj line 1)
(25085) first adj Gate
(25613) second adj Gate
(882216) charge
(45481) charge adj stor \$4
(95402) ono
(345908) nitride ono
(595) (nitride ono) near4 (charge adj stor \$4)
(11094) (first adj Gate) near9 (second adj Gate)
(78) ((first adj Gate) near9 (second adj Gate)) near8 ((perpendicular \$2 orthogonal \$3))
(0) (((first adj Gate) near9 (second adj Gate)) near8 ((perpendicular \$2 orthogonal \$3))
(182) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(0) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(0) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(13) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(187) two adj (charge adj stor \$4)
(3) ((channel with ((bl bitline bit adj line 1)
(208) (punch adj through) adj region
(31) ((channel with ((bl bitline bit adj line 1)
(35) (punch adj through) adj region) and ((nitride ono) near4 (charge adj stor \$4))
(3) ((sonos monos) ono) same (punch adj through) adj region
(41) ((sonos monos) ono) and ((punch adj through) adj region)
(6) ((sonos monos) ono)

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2	F	Kamigaki, Yo	US 6674122	20040	8	Semiconductor integrated circuit	257/326	257/324			F	F	F	F	F		US 6674122	
3	F	Fujiwara, Ichi	US 6874120	20040	4	Nonvolatile semiconductor memory device a	257/324	257/318			F	F	F	F	F		US 6874120	
4	F	Shukuri, Shoji	US 2003019	20031	9	Semiconductor integrated circuit device and	365/185				F	F	F	F	F		US 2003019	
5	F	Sugita, Yasuh	US 2002004	20020	2	Nonvolatile semiconductor memory device, p	365/200				F	F	F	F	F		US 2002004	
6	F	Fujiwara, Ichi	US 6717880	20040	3	Method of erasing non-volatile semiconducto	365/185	365/185	29		F	F	F	F	F		US 6717880	
7	F	Eitan, Boaz	US 6566689	20030	2	Non-volatile electrically erasable and progr	257/296	257/380			F	F	F	F	F		US 6566689	
8	F	Kobayashi, T	US 6563728	20030	2	Semiconductor memory device and method f	365/83	257/E21	67		F	F	F	F	F		US 6563728	
9	F	Sugita, Yasuh	US 6531732	20030	2	Nonvolatile semiconductor memory device, p	257/315	257/318			F	F	F	F	F		US 6531732	
10	F	Fujiwara, Ichi	US 6434053	20020	5	Nonvolatile semiconductor memory device, p	365/185	257/324			F	F	F	F	F		US 6434053	

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